

FIG. 1

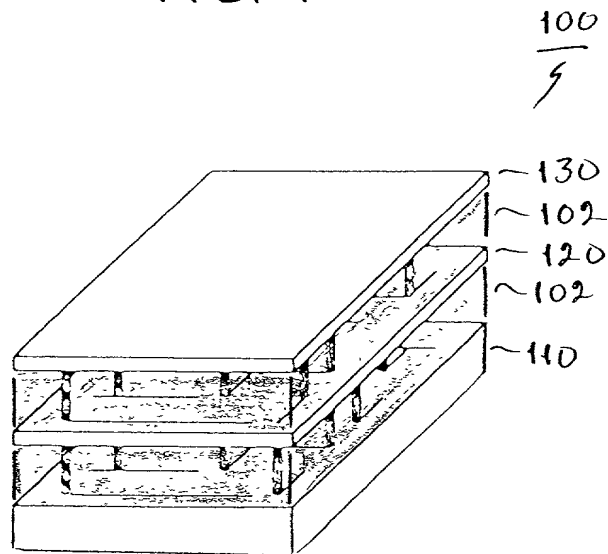
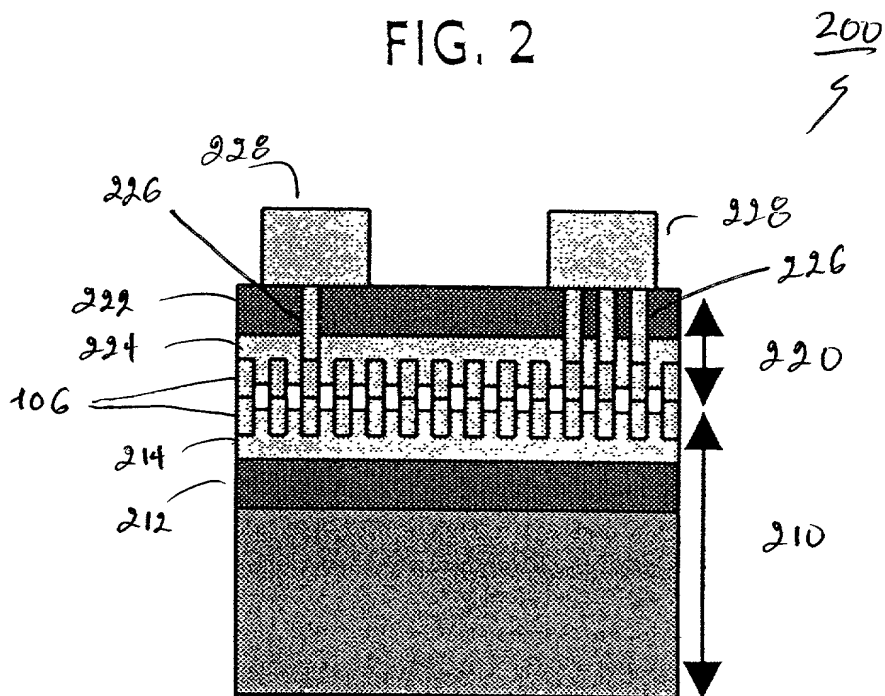


FIG. 2





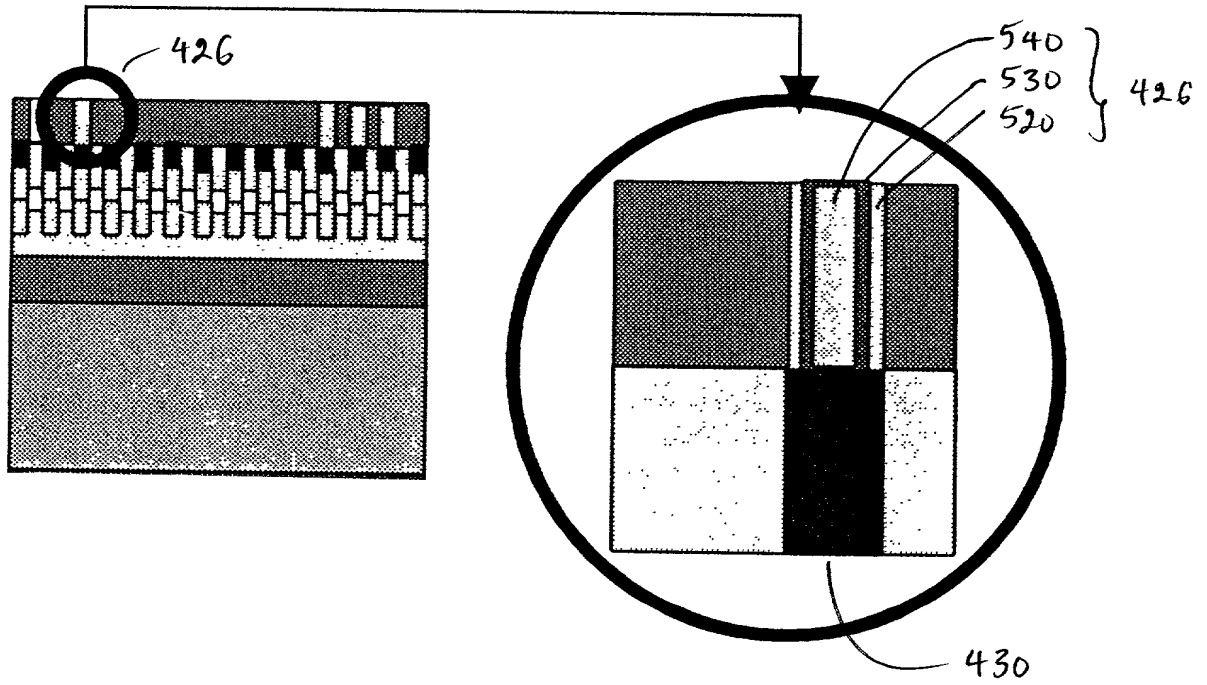
[illegible]

A cross-sectional view of a semiconductor device 106. The device consists of a substrate 412, a first conductive layer 414, and a second conductive layer 420. A patterned layer 422 is formed on the second conductive layer 420, with a patterned layer 424 on top of it. A patterned layer 426 is formed on the patterned layer 424, with a patterned layer 428 on top of it. A patterned layer 430 is formed on the patterned layer 428. A lightning bolt symbol 400 is shown above the patterned layer 430. A double-headed arrow 410 indicates the thickness of the substrate 412.



# FIG. 5C

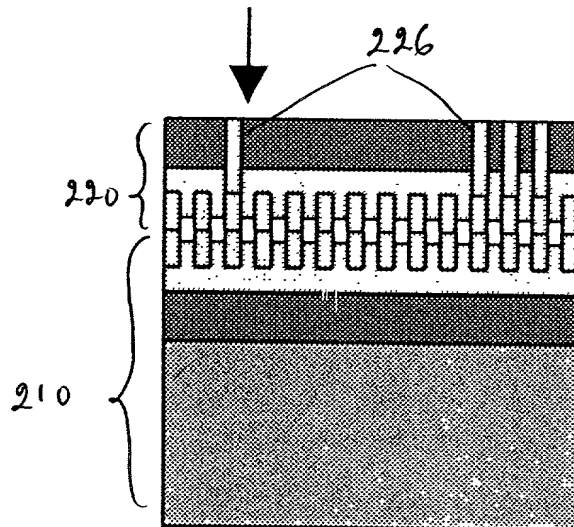
400



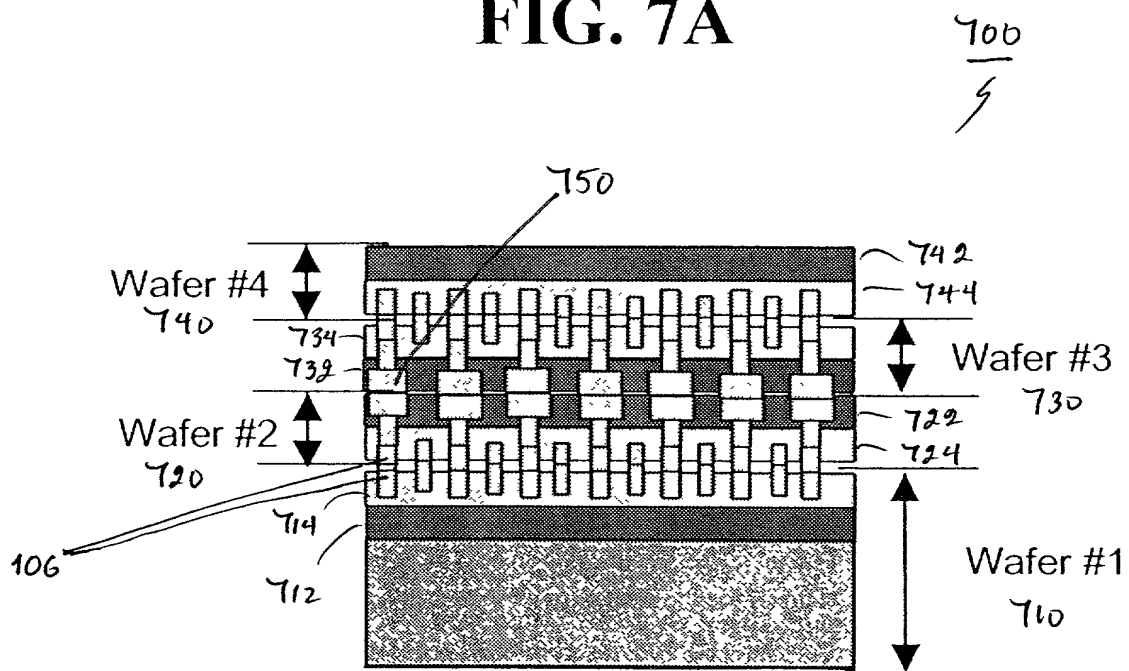
# FIG. 6

Si Via that processed during STI steps

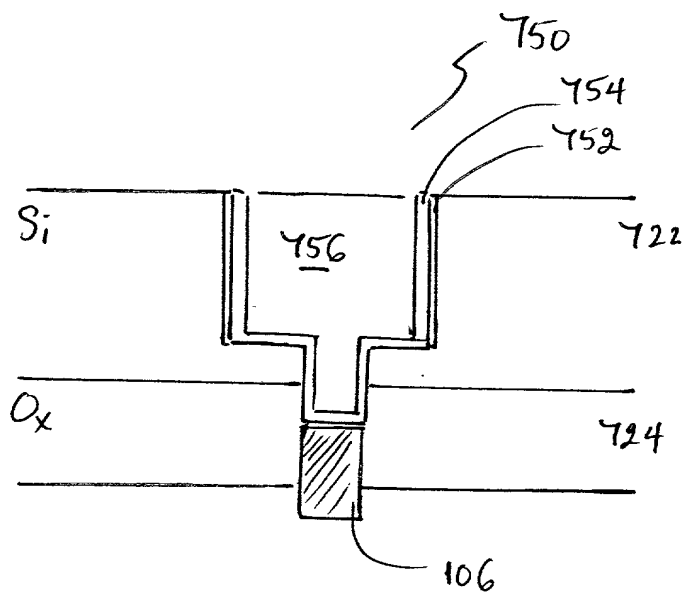
200



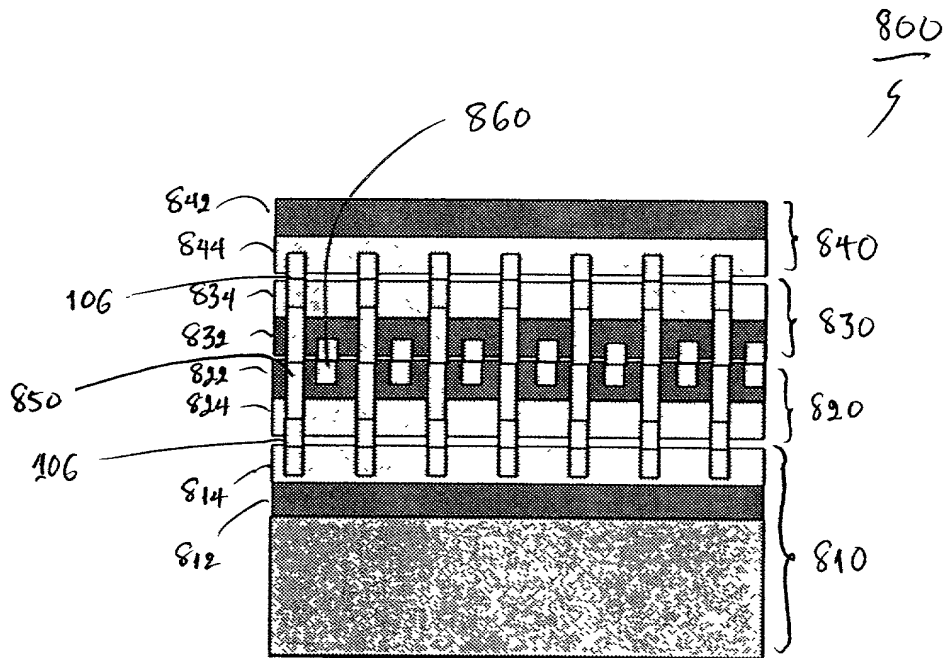
# FIG. 7A



# FIG. 7B



# FIG. 8



# FIG. 9

